

## Refine Search

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adjacent near10 (TFT near10 capacitor)	61

Database:

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 US Patents Full-Text Database  
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### Search History

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	DB=USPT; PLUR=YES; OP=OR		
<u>L25</u>	adjacent near10 (TFT near10 capacitor)	61	<u>L25</u>
	DB=PGPB; PLUR=YES; OP=OR		
<u>L24</u>	adjacent near10 (TFT near10 capacitor)	40	<u>L24</u>
<u>L23</u>	L22 and (((dielectric near5 thickness) near10 "same") same ("gate dielectric" or "gate insulation"))	0	<u>L23</u>
<u>L22</u>	TFT same capacitor	4547	<u>L22</u>
	DB=USPT; PLUR=YES; OP=OR		
<u>L21</u>	L20 and (("gate electrode" near10 "conductivity type") same (capacitor near6 (electrode or plate)))	0	<u>L21</u>
<u>L20</u>	L15 and (((dielectric near5 thickness) near10 "same") same ("gate dielectric" or "gate insulation"))	6	<u>L20</u>
<u>L19</u>	L15 (((dielectric near5 thickness) near10 "same") same ("gate dielectric" or "gate insulation"))	3728	<u>L19</u>

<a href="#"><u>L18</u></a>	L15 same ("same conductivity" near10 (active) same (capacit\$5 near5 (plate or electrode)))	1	<a href="#"><u>L18</u></a>
<a href="#"><u>L17</u></a>	L15 and ("same conductivity" near10 (active) near10 (capacit\$5 near5 (plate or electrode)))	0	<a href="#"><u>L17</u></a>
<a href="#"><u>L16</u></a>	L15 ("same conductivity" near10 (active) near10 (capacit\$5 near5 (plate or electrode)))	3567	<a href="#"><u>L16</u></a>
<a href="#"><u>L15</u></a>	TFT same capacitor	3567	<a href="#"><u>L15</u></a>
<a href="#"><u>L14</u></a>	"quantum well" near16 (InGaN near5 thickness) near20 AlInGaN	0	<a href="#"><u>L14</u></a>
<a href="#"><u>L13</u></a>	L7 and (Al near7 (composition or percentage or concentration))	4	<a href="#"><u>L13</u></a>
<a href="#"><u>L12</u></a>	"quantum well" near13 (InGaN near5 thickness) near15 AlInGaN	0	<a href="#"><u>L12</u></a>
<a href="#"><u>L11</u></a>	L9 and thickness	7	<a href="#"><u>L11</u></a>
<a href="#"><u>L10</u></a>	L6 and thickness	14	<a href="#"><u>L10</u></a>
<a href="#"><u>L9</u></a>	L7 and (In near7 (composition or percentage or concentration))	7	<a href="#"><u>L9</u></a>
<a href="#"><u>L8</u></a>	L7 and (In near7 (composition or percentage))	5	<a href="#"><u>L8</u></a>
<a href="#"><u>L7</u></a>	L2 and (("quantum well") same (InGaN) same AlInGaN)	14	<a href="#"><u>L7</u></a>
<a href="#"><u>L6</u></a>	L2 and (("quantum well") same (InGaN) same AlInGaN)	14	<a href="#"><u>L6</u></a>
<a href="#"><u>L5</u></a>	L2 and (multilayer\$5 same ("quantum well") same (InGaN) same AlInGaN)	0	<a href="#"><u>L5</u></a>
<a href="#"><u>L4</u></a>	L2 and (multilayer\$5 near4 ("quantum well"))	9	<a href="#"><u>L4</u></a>
<a href="#"><u>L3</u></a>	L2 and ("quantum well")	536	<a href="#"><u>L3</u></a>
<a href="#"><u>L2</u></a>	L1 and substrate	1194	<a href="#"><u>L2</u></a>
<a href="#"><u>L1</u></a>	("gallium nitride" or GaN) same LED	1321	<a href="#"><u>L1</u></a>

END OF SEARCH HISTORY